New Jersey Semi-Conductor Products, Inc.

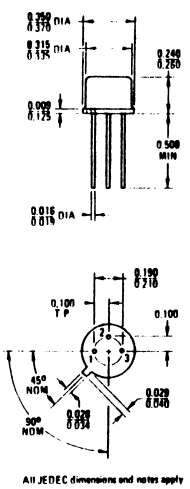
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2N6376 (SILICON)

NPN SILICON HIGH-FREQUENCY TRANSISTOR

TO-39



MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CB}	75	Vdc
Emitter-Base Voltage	V_{EB}	5	Vdc
Collector Current	I_C	0.4	Amp
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (I_C = 5.0 mAdc, I_B = 0)	$BV_{CEO(sus)}$	40			Vdc
Collector-Base Breakdown Voltage (I_E = 0, I_C = 0.1 mAdc)	BV_{CBO}	75			Vdc
Emitter-Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)	BV_{EBO}	5			Vdc
Collector Cutoff Current (V_{CE} = 28 Vdc, I_B = 0)	I_{EBO}			100	μAdc
Collector Cutoff Current (V_{CE} = 55 Vdc, V_{BE} = 1.5 Vdc)	I_{CBO}			200	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	30		125	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 20 mAdc)	$V_{CE(sat)}$			1.0	Vdc

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